

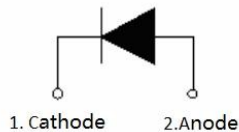
S4D30120H 1200V SiC POWER SCHOTTKY RECTIFIER



Description

S4D30120H is a SiC Schottky rectifier packaged in TO-247AC(TO-247-2) case. The device is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D30120H is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- “-A” is an AEC-Q101 qualified device
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	1200	V
Average Rectified Forward Current	$I_{F(AV)1}$	$T_C = 25^\circ C$	94	A
	$I_{F(AV)2}$	$T_C = 155^\circ C$	30	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM1}	10ms, Half Sine pulse, $T_C = 25^\circ C$	300	A
	I_{FSM2}	10ms, Half Sine pulse, $T_C = 110^\circ C$	246	A
Repetitive Peak Forward Surge Current	I_{FRM1}	10ms, Half Sine pulse, $T_C = 25^\circ C$	121	A
	I_{FRM2}	10ms, Half Sine pulse, $T_C = 110^\circ C$	68	A
Power Dissipation	P_{tot1}	$T_C = 25^\circ C$	441	W
	P_{tot2}	$T_C = 110^\circ C$	191	W
I ² t Value	$\int i^2 t_1$	10ms, $T_C = 25^\circ C$	271	A ² s
	$\int i^2 t_2$	10ms, $T_C = 25^\circ C$	218	A ² s

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 30A, Pulse, T _J = 25 °C	1.5	1.8	V
	V _{F2}	@ 30A, Pulse, T _J = 175 °C	2.2	3.0	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	1	20	uA
	I _{R2}	@V _R = rated V _R , T _J = 175 °C	5	200	uA
Junction Capacitance	C _T	V _R =0V, f=1MHz, T _J =25°C,	2581	-	pF
Reverse Recovery Charge	Q _c	V _R = 800 V, T _J = 25°C	152	-	nC
Capacitance Stored Energy	E _C	V _R = 800 V, T _J = 25°C	44	-	μJ

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation, T _J =25°C	0.34	°C/W

Electrostatic Discharge (ESD) Classifications:

Parameter	Symbol	Value
Human Body Model	HBM	Class 3B (≥ 8000 V)
Charge Device Model	CDM	Class C3 (≥ 1000 V)

Ordering Information

Device	Package	Shipping
S4D30120H	TO-247AC(TO-247-2)	25pcs / tube

Ratings and Characteristics Curves

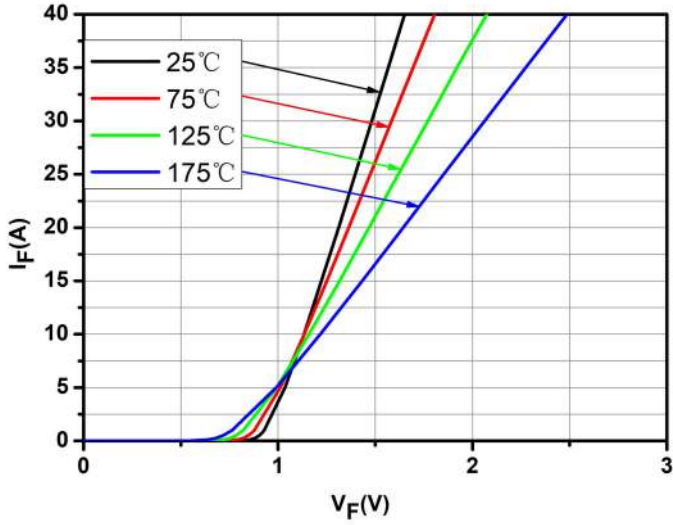


Fig.1-Typical Forward Voltage Characteristics

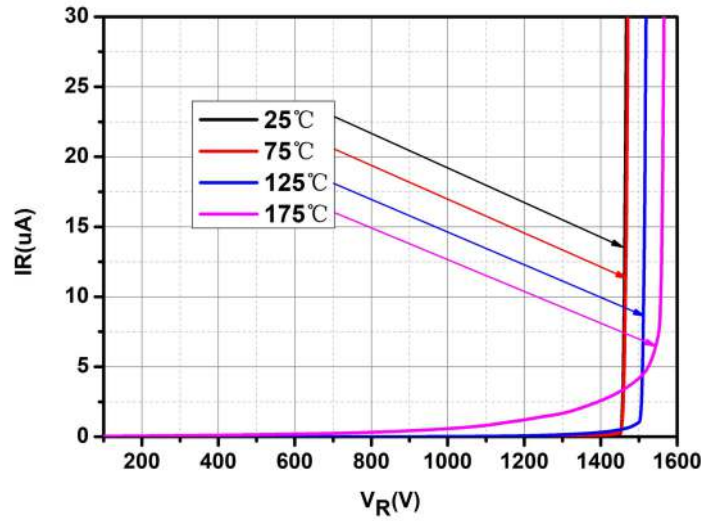


Fig.2-Typical Reverse Characteristics

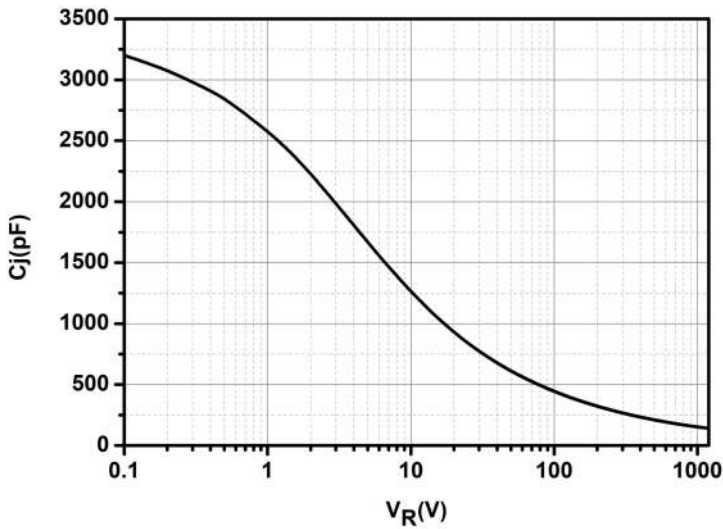


Fig.3-Capacitance vs. Reverse Voltage

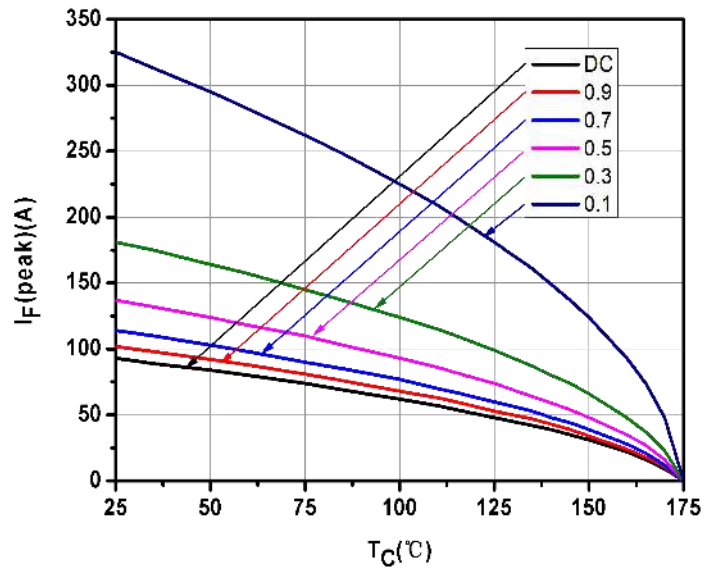


Fig.4-Current Derating

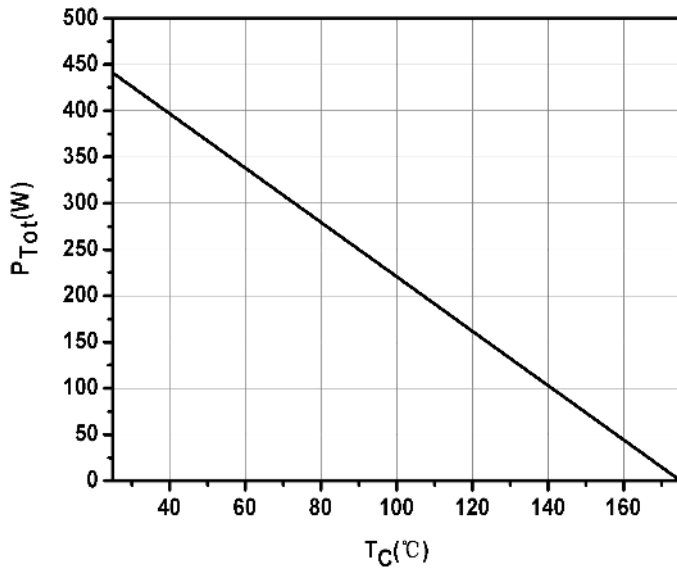


Fig.5-Power Derating

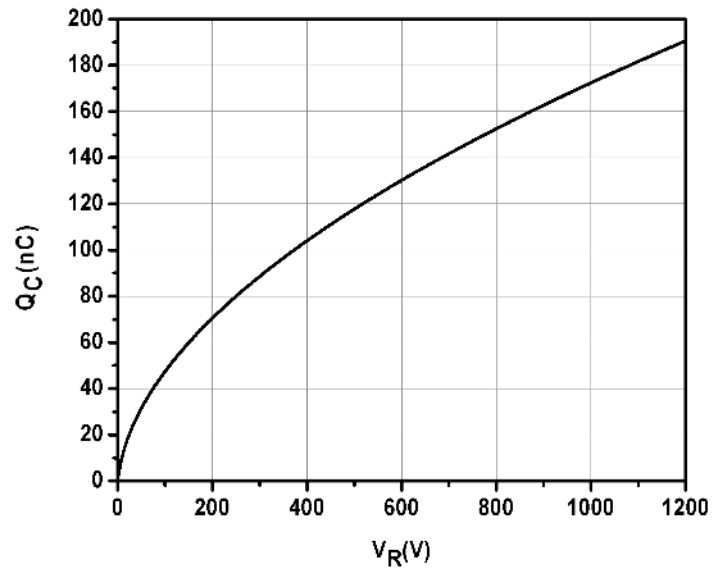


Fig.6-Total Capacitance Charge vs. Reverse Voltage

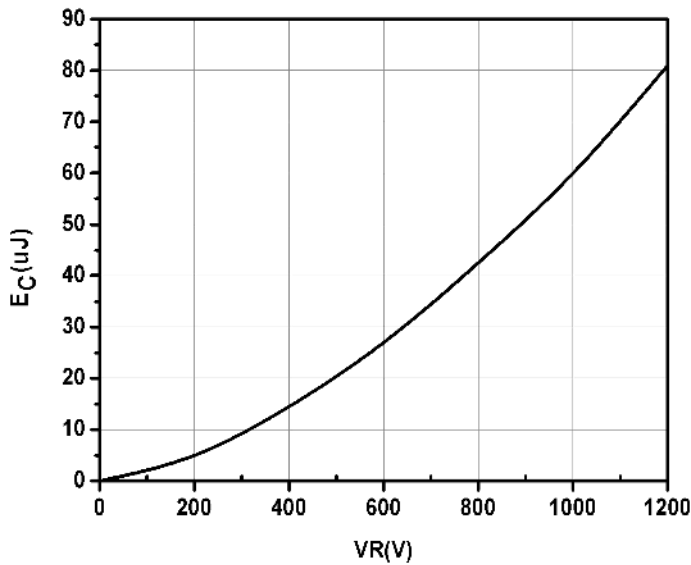
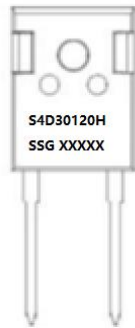


Fig.7-Capacitance Stored Energy

Marking Diagram

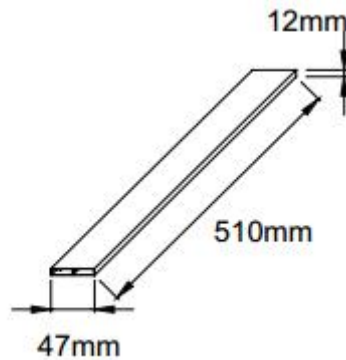


Where XXXXX is YYWWL

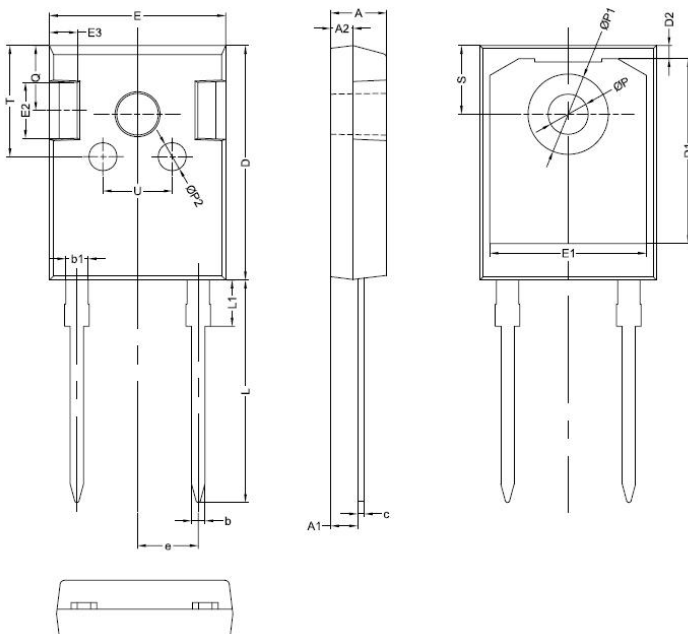
- S4D = Device Type
- H = Package type
- 30 = Forward Current (30A)
- 120 = Reverse Voltage (1200V)
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Tube Specification(TO-247AC(TO-247-2))



Mechanical Dimensions TO-247AC(TO-247-2)



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1	1.80	2.00	2.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	7.1	7.19	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

Technical Data
Data Sheet N2417, REV.D



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